# N-Channel 120-V (D-S) MOSFET

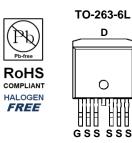
### **Key Features:**

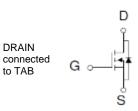
- Low r<sub>DS(on)</sub> trench technology
- Low thermal impedance
- · Fast switching speed

### **Typical Applications:**

- LED Inverter Circuits
- DC/DC Conversion Circuits
- Motor drives

PRODUCT SUMMARY				
Vds (V)	$r_{DS(on)}(m\Omega)$	I⊳(A)		
120	10 @ V <sub>GS</sub> = 10V	90 <sup>a</sup>		
	14 @ V <sub>GS</sub> = 6.5V	90		





N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^{\circ}C$ UNLESS OTHERWISE NOTED)						
Parameter			Limit	Units		
Drain-Source Voltage			120	V		
Gate-Source Voltage			±20	v		
Continuous Drain Current <sup>a</sup>	T <sub>C</sub> =25°C	I <sub>D</sub>	90			
Pulsed Drain Current <sup>b</sup>		I <sub>DM</sub>	360	A		
Continuous Source Current (Diode Conduction) <sup>a</sup>	T <sub>C</sub> =25°C	I <sub>S</sub>	90	А		
Power Dissipation <sup>a</sup>	T <sub>C</sub> =25°C	PD	300	W		
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to 175	°C		

THERMAL RESISTANCE RATINGS			
Parameter	Symbol	Maximum	Units
Maximum Junction-to-Ambient °	R <sub>θJA</sub>	62.5	°C/W
Maximum Junction-to-Case	$R_{ extsf{ heta}JC}$	0.5	C/W

Notes

- a. Package Limited
- b. Pulse width limited by maximum junction temperature
- c. Surface Mounted on 1" x 1" FR4 Board.

### **Electrical Characteristics**

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_D = 250 \text{ uA}$	1			V	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V},  V_{GS} = \pm 20 \text{ V}$			±100	nA	
Zero Gate Voltage Drain Current		$V_{\text{DS}} = 96 \text{ V},  V_{\text{GS}} = 0 \text{ V}$			1		
Zero Gale voltage Drain Current	I <sub>DSS</sub>	$V_{DS} = 96 \text{ V}, \text{ V}_{GS} = 0 \text{ V}, \text{ T}_{J} = 55^{\circ}\text{C}$			10	uA	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} = 5 V, V_{GS} = 10 V$	110			А	
Drain-Source On-Resistance <sup>a</sup>	r	$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 40 \text{ A}$			10	mΩ	
Drain-Source On-Resistance	r <sub>DS(on)</sub>	$V_{GS} = 6.5 \text{ V}, I_{D} = 30 \text{ A}$			14		
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	$V_{DS} = 15 \text{ V}, \text{ I}_{D} = 40 \text{ A}$		65		S	
Diode Forward Voltage <sup>a</sup>	V <sub>SD</sub>	$I_{\rm S} = 40$ A, $V_{\rm GS} = 0$ V		0.91		V	
		Dynamic <sup>b</sup>					
Total Gate Charge	$Q_g$	V <sub>DS</sub> = 60 V, V <sub>GS</sub> = 6.5 V,		30		nC	
Gate-Source Charge	$Q_{gs}$	$v_{\rm DS} = 60  v,  v_{\rm GS} = 6.3  v,$ $I_{\rm D} = 40  {\rm A}$		13			
Gate-Drain Charge	$Q_{gd}$	10 - 40 / 1		12		1	
Turn-On Delay Time	t <sub>d(on)</sub>	$\gamma = 0$		17			
Rise Time	t <sub>r</sub>	$V_{DS} = 60 \text{ V}, \text{ R}_{L} = 1.5 \Omega,$ $I_{D} = 40 \text{ A},$		16		20	
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{\text{GEN}} = 10 \text{ V}, \text{ R}_{\text{GEN}} = 6 \Omega$		47		ns	
Fall Time	t <sub>f</sub>	$V_{\text{GEN}} = 10$ V, $V_{\text{GEN}} = 0.22$		68			
Input Capacitance	C <sub>iss</sub>			2318			
Output Capacitance	C <sub>oss</sub>	$V_{DS}$ = 50 V, $V_{GS}$ = 0 V, f = 1 Mhz		585		pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	1		24			

#### Notes

- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

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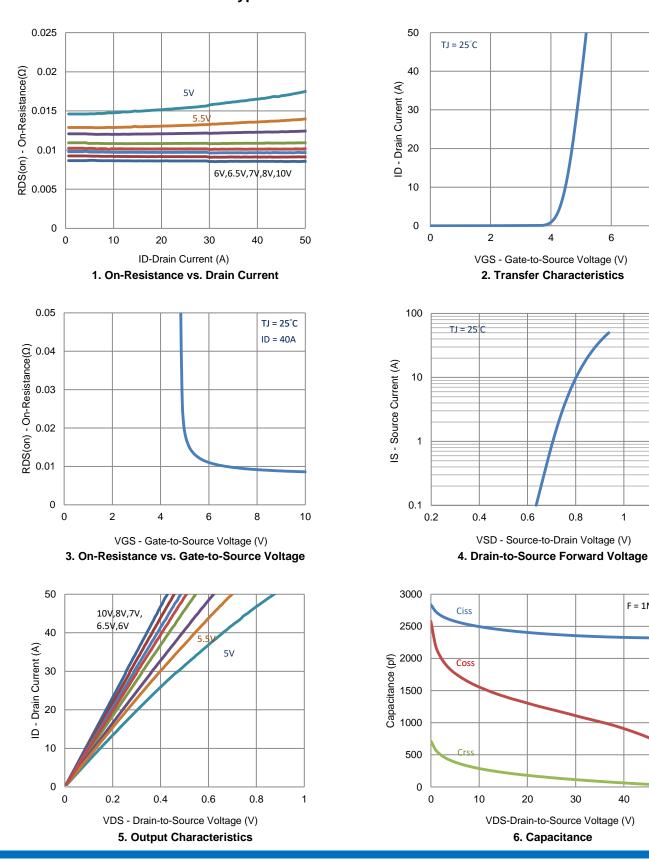
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1

F = 1MHz

1.2

8

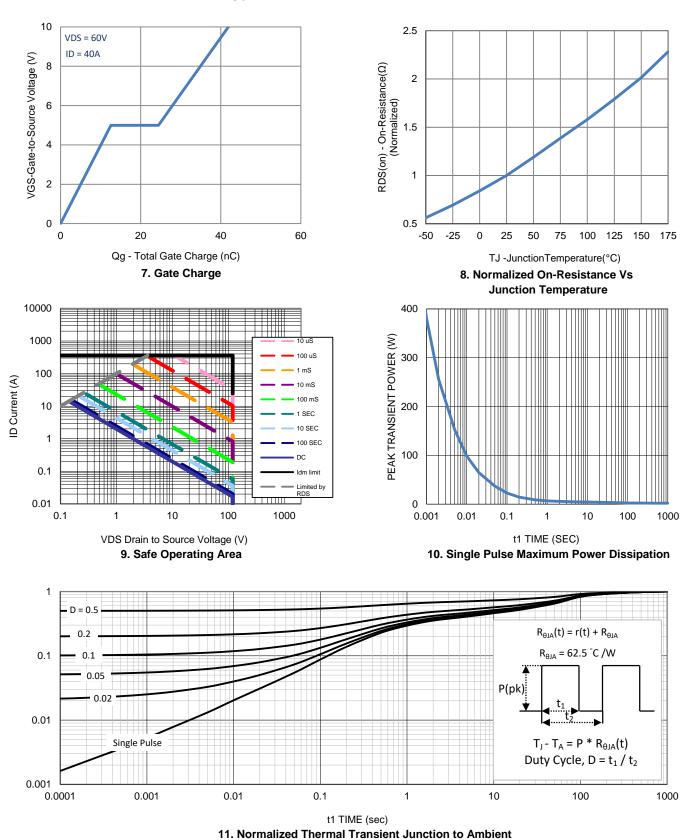


### **Typical Electrical Characteristics**

Publication Order Number: DS\_AM90N12-10B6L\_1A

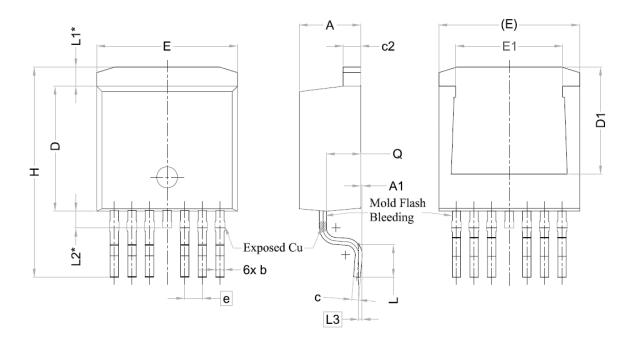
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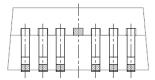
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### **Typical Electrical Characteristics**

## **Package Information**





SYMBOL	DIMENSIONS			
STIVIDOL	MIN.	NOM.	MAX.	
A	4.24	4.44	4.64	
A1	0.00	0.10	0.25	
b	0.50	0.60	0.70	
с	0.40 0.50		0.60	
c2	1.15	1.27	1.40	
D	8.82	8.92	9.02	
D1	6.86	7.65	_	
E	9.96	10.16	10.36	
E1	6.89 7.77		7.89	
е	1.27 BSC			
н	14.61	15.00	15.88	
L	1.78	2.32	2.79	
L1	1.36 REF.			
L2	1,20 REF.			
L3	0.25 BSC			
Q	2.30	2.70		